Vishay Siliconix

Automotive Dual N-Channel 60 V (D-S) 175 °C MOSFET

DESCRIPTION

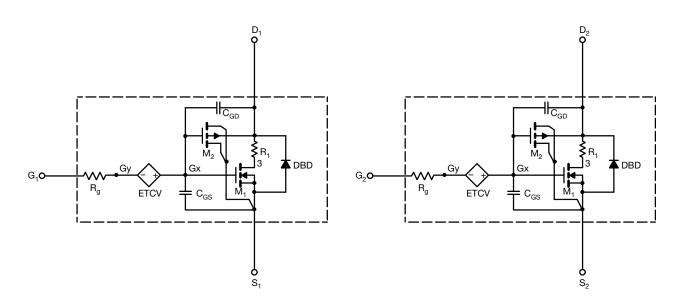
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over the -55 °C to 125 °C temperature range
- Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



SPICE Device Model SQJ952EP

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	2	V
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 10.3 \text{ A}$	0.013	0.012	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 10.3 \text{ A}$	0.016	0.016	
Forward transconductance a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 10.3 \text{ A}$	57	68	S
Diode forward voltage	V_{SD}	I _S = 10.3 A	0.81	0.80	V
Dynamic ^b					
Input capacitance	C _{iss}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	1520	1500	pF
Output capacitance	C _{oss}		138	130	
Reverse transfer capacitance	C _{rss}		57	55	
Total gate charge	Q_g	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 4.5 \text{ A}$	24	24	nC
Gate-source charge	Q _{gs}		4	5	
Gate-drain charge	Q _{gd}		9	12	

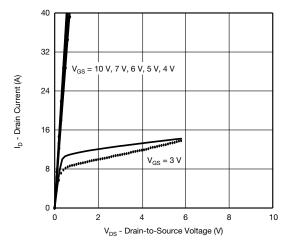
Notes

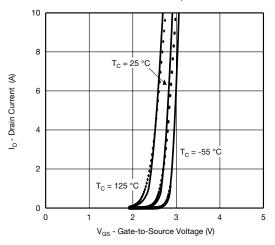
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

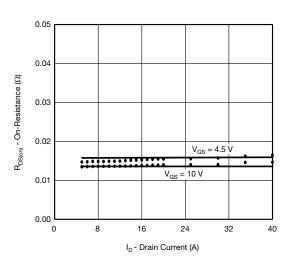
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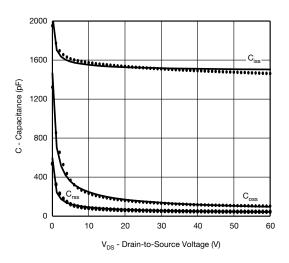
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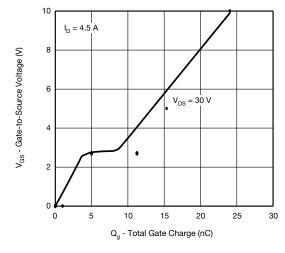
COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25~^{\circ}\text{C}$, unless otherwise noted)

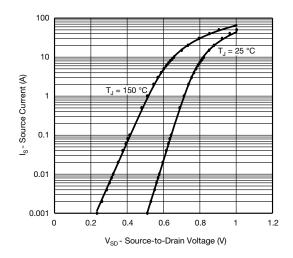












Note

 Dots and squares represent measured data Copyright: Vishay Intertechnology, Inc.



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